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Vishay/Siliconix
SUP40N10-30-GE3

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SUP40N10-30-GE3

Vishay Siliconix

N-Channel 100 V (D-S) MOSFET

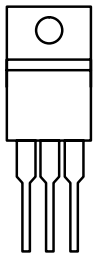
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
100	0.030 at V_{GS} = 10 V	38.5
	0.034 at V_{GS} = 6 V	36

FEATURES

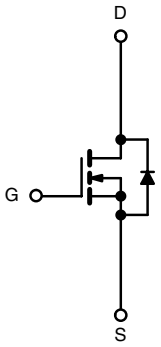
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT
HALOGEN FREE Available

TO-220AB



Top View



N-Channel MOSFET

Ordering Information: SUP40N10-30-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	38.5	A
	T_C = 125 °C		17	
Pulsed Drain Current		I_{DM}	75	
Avalanche Current		I_{AS}	35	
Single Pulse Avalanche Energy[a]	L = 0.1 mH	E_{AS}	61	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	89[b]	W
	T_A = 25 °C[c]		3.1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Limit**	**Unit**
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	40	°C/W
	Free Air		62.5	
Junction-to-Case (Drain)		R_{thJC}	1.4	

Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR-4 material).

SUP40N10-30-GE3

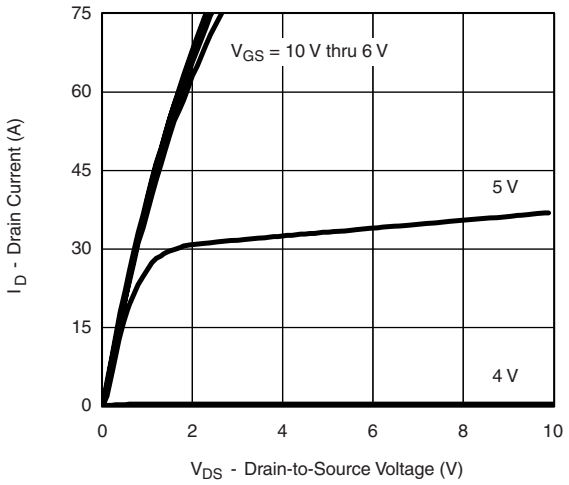
Vishay Siliconix

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V			1	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 150 °C			150	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	75			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15 A		0.024	0.030	Ω
		V_{GS} = 6 V, I_D = 10 A		0.026	0.034	
		V_{GS} = 10 V, I_D = 15 A, T_J = 125 °C			0.054	
		V_{GS} = 10 V, I_D = 15 A, T_J = 150 °C			0.060	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 15 A	10			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2400		pF
Output Capacitance	C_{oss}			270		
Reverse Transfer Capacitance	C_{rss}			90		
Total Gate Charge[c]	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 40 A		35	60	nC
Gate-Source Charge[c]	Q_{gs}			11		
Gate-Drain Charge[c]	Q_{gd}			9		
Gate Resistance	R_g			1.7		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 50 V, R_L = 1.25 Ω I_D ≅ 40 A, V_{GEN} = 10 V, R_g = 2.5 Ω		11	20	ns
Rise Time[c]	t_r			12	20	
Turn-Off Delay Time[c]	$t_{d(off)}$			30	45	
Fall Time[c]	t_f			12	20	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				40	A
Pulsed Current	I_{SM}				75	
Forward Voltage[a]	V_{SD}	I_F = 30 A, V_{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 30 A, dI/dt = 100 A/µs		60	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			5	8	A
Reverse Recovery Charge	Q_{rr}			0.15	0.4	µC

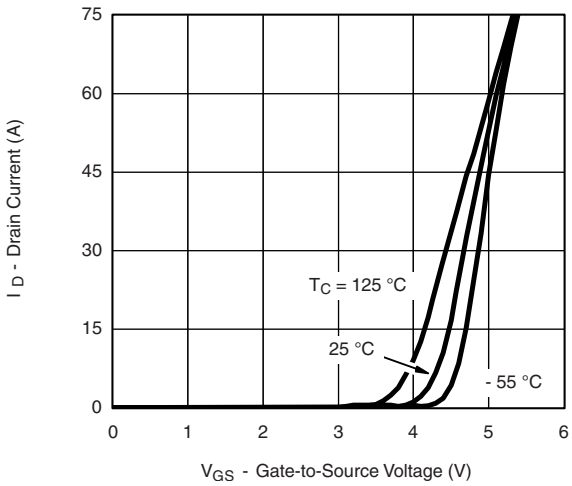
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

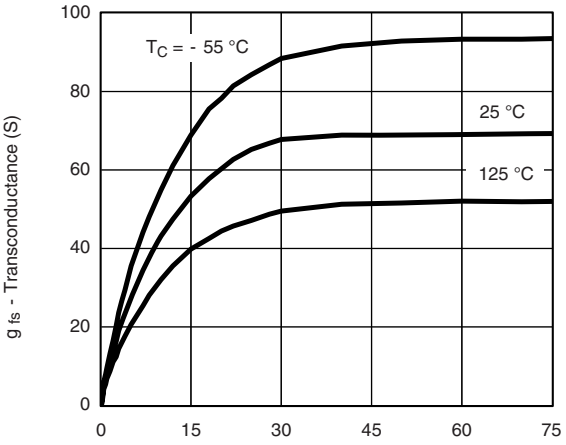
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



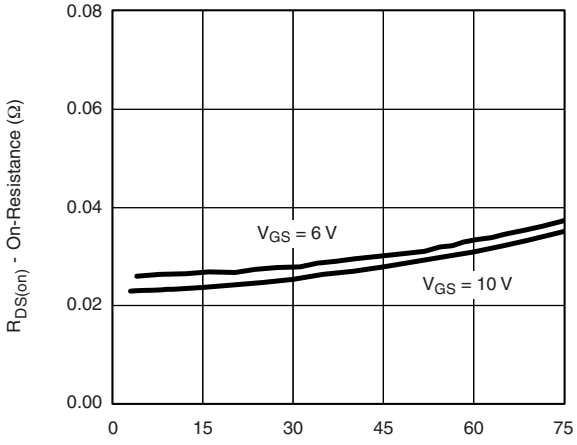
Output Characteristics



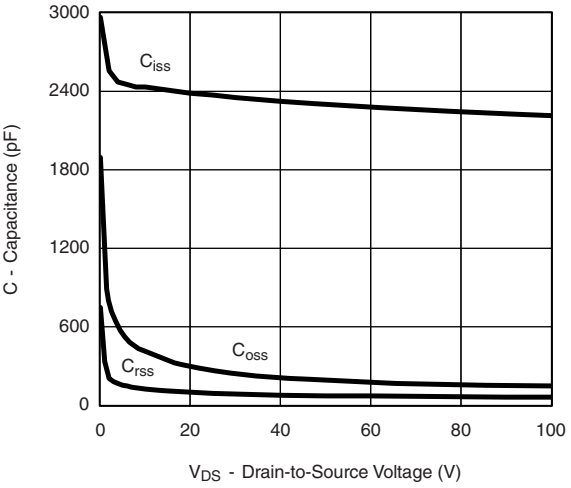
Transfer Characteristics



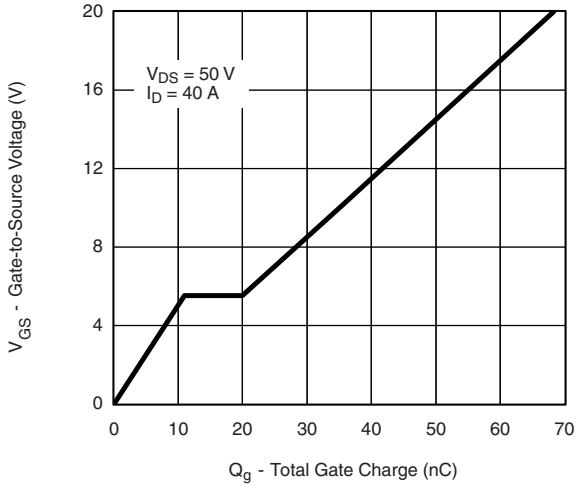
Transconductance



On-Resistance vs. Drain Current

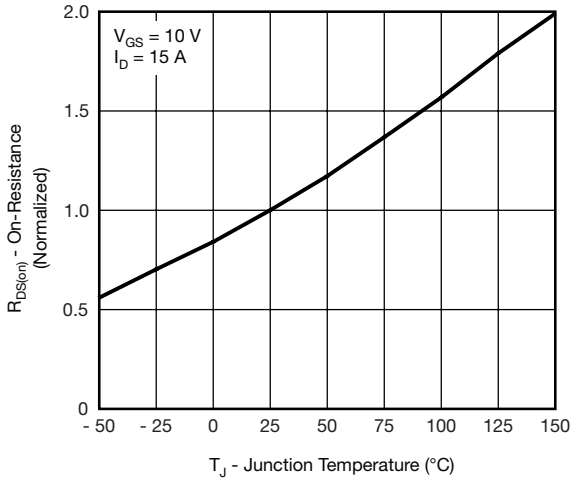


Capacitance

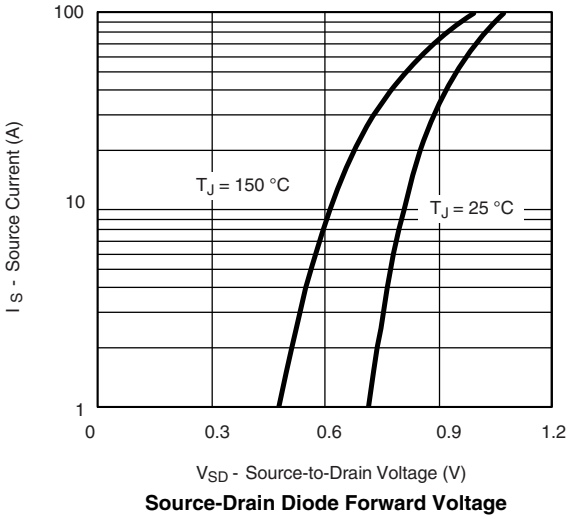


Gate Charge

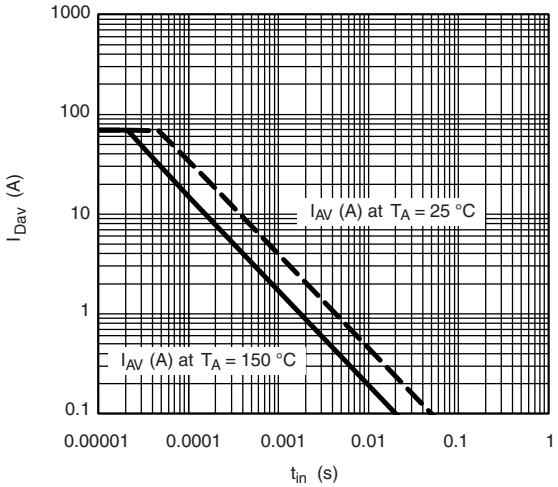
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



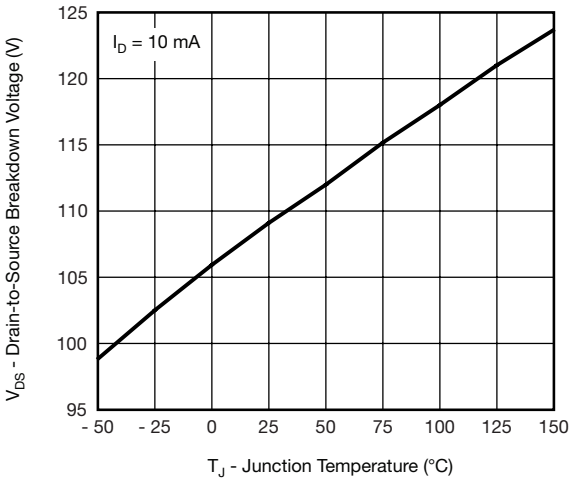
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

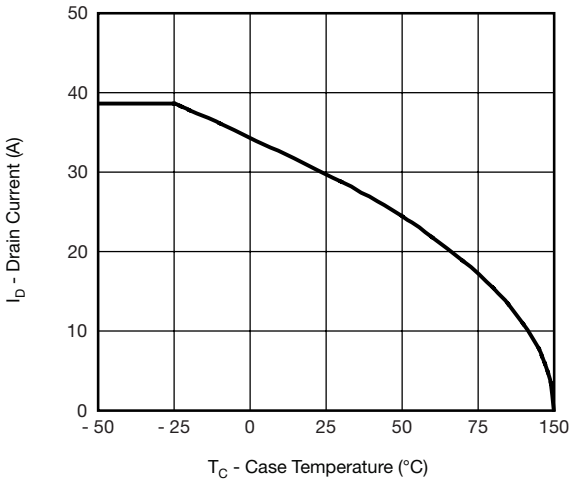


Avalanche Current vs. Time

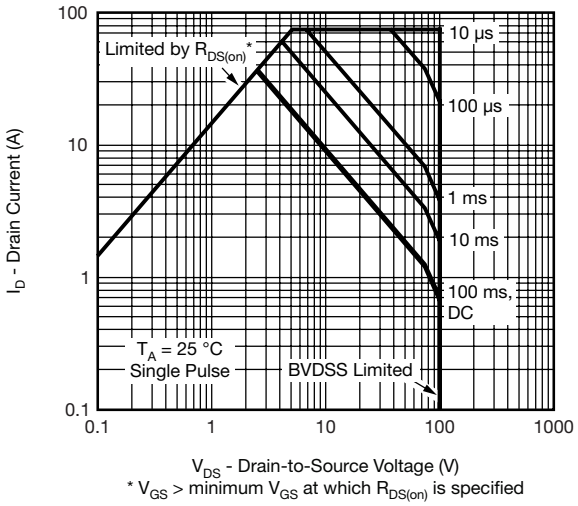


Drain-Source Breakdown Voltage vs. Junction Temperature

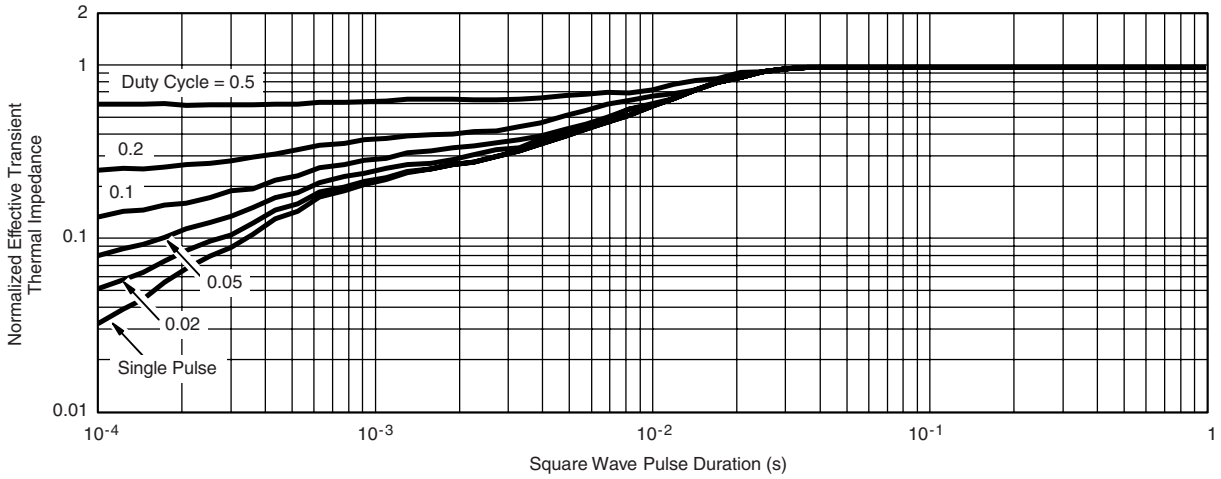
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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